



THERMAL CHARACTERISTICS

Parameter	Symbol	Тур	Max	Units
Thermal Resistance Junction-to-Case (Note 2)	$R_{ heta JC}$	0.88	_	°C/W

Thermal Resistance Junction-to-Ambient (Notes 1, 2)

ELECTRICAL CHARACTERISTICS (T_{.I} = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
SOURCE-DRAIN DIODE CHARACTERIST	ics					
Reverse Recovery Time	^t RR	$V_{GS} = -5/18 \text{ V}, I_{SD} = 20 \text{ A},$ $dI_S/dt = 1000 \text{ A/}\mu\text{s}$		17.7		

TYPICAL CHARACTERISTICS

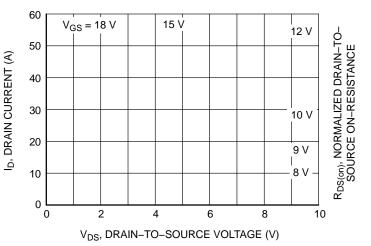
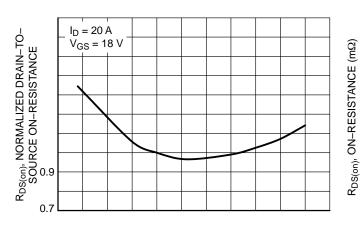
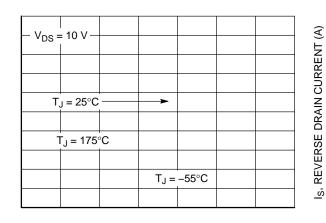


Figure 1. On-Region Characteristics



T_J, JUNCTION TEMPERATURE (°C)

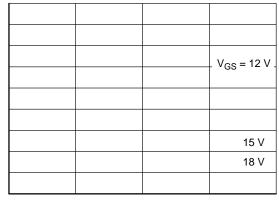
Figure 3. On–Resistance Variation with Temperature



ID, DRAIN CURRENT (A)

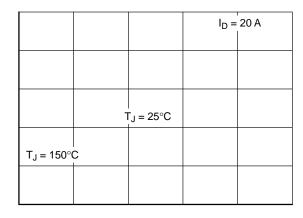
V_{GS}, GATE-TO-SOURCE VOLTAGE (V)

Figure 5. Transfer Characteristics



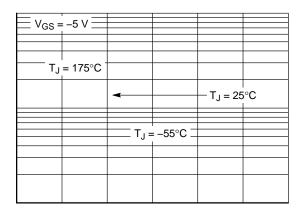
ID, DRAIN CURRENT (A)

Figure 2. Normalized On–Resistance vs. Drain Current and Gate Voltage



V_{GS}, GATE-TO-SOURCE VOLTAGE (V)

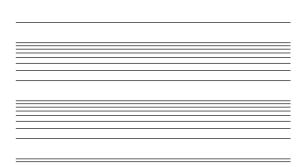
Figure 4. On-Resistance vs. Gate-to-Source Voltage



V_{SD}, BODY DIODE FORWARD VOLTAGE (V)

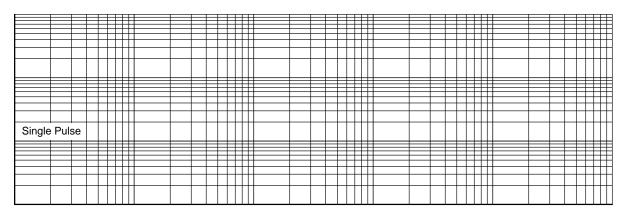
Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

 $Z_{\theta JC}$, EFFECTIVE TRANSIENT THERMAL RESISTANCE (°C/W)



t, PULSE TIME (s)

Figure 13. Junction-to-Case Transient Thermal Response

D²PAK7 (TO-263-7L HV) CASE 418BJ ISSUE B

DATE 16 AUG 2019

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GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

